Octal 3-State Noninverting D Flip-Flop

High-Performance Silicon-Gate CMOS

The 74HC574 is identical in pinout to the LS574. The device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs.

Data meeting the set-up time is clocked to the outputs with the rising edge of the Clock. The Output Enable input does not affect the states of the flip-flops but when Output Enable is high, all device outputs are forced to the high-impedance state. Thus, data may be stored even when the outputs are not enabled.

The HC574 is identical in function to the HC374A but has the flip-flop inputs on the opposite side of the package from the outputs to facilitate PC board layout.

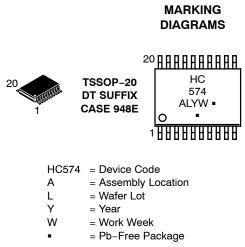
Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 µA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 266 FETs or 66.5 Equivalent Gates
- This is a Pb–Free Device



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(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

OUTPUT	1•	20	□ v _{cc}
D0	2	19] Q0
D1 [3	18] Q1
D2 [4	17] Q2
D3 [5	16] Q3
D4 [6	15] Q4
D5 [7	14] Q5
D6 [8	13] Q6
D7 [9	12] Q7
GND [10	11	сгоск
	-		•

FUNCTION TABLE

Inputs			Output
OE	Clock	D	Q
L	7	Н	Н
L		L	L
L	L,H, ╲_	Х	No Change
Н	Х	Х	Z

X = Don't Care

Z = High Impedance

Figure 1. Pin Assignment

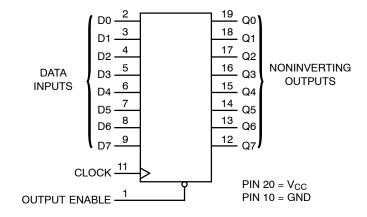


Figure	2. L	oaic	Diagram
			- agrain

Design Criteria	Value	Units
Internal Gate Count*	66.5	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	0.0075	рJ

*Equivalent to a two-input NAND gate.

MAXIMUM RATINGS

Symbol		Parameter	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		-0.5 to $V_{CC}+0.5$	V
Vo	DC Output Voltage	(Note 1)	-0.5 to $V_{CC}+0.5$	V
I _{IK}	DC Input Diode Current		±20	mA
I _{OK}	DC Output Diode Current	±35	mA	
Ι _Ο	DC Output Sink Current		±35	mA
I _{CC}	DC Supply Current per Supply Pin		±75	mA
I _{GND}	DC Ground Current per Ground Pir	1	±75	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Cas	e for 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+ 150	°C
θ_{JA}	Thermal Resistance	TSSOP	128	°C/W
PD	Power Dissipation in Still Air at 85°	C TSSOP	450	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% – 35%	UL 94 V-0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	>2000 >200	V
I _{Latchup}	Latchup Performance	Above V _{CC} and Below GND at 85 $^{\circ}$ C (Note 4)	± 300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
1. I_O absolute maximum rating must be observed.

2. Tested to EIA/JESD22-A114-A.

3. Tested to EIA/JESD22-A115-A.

4. Tested to EIA/JESD78.

5. For high frequency or heavy load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage	(Referenced to GND)	2.0	6.0	V
V _I , V _O	DC Input Voltage, Output Voltage	(Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types		- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 3)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

6. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

ORDERING INFORMATION

Device	Package	Shipping [†]	
74HC574DTR2G	TSSOP-20*	2500 / Tape & Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

	Parameter		V _{CC}	Guara			
Symbol		Test Conditions	(V)	-55 to 25°C	≤ 85°C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$\begin{array}{l} V_{out} = V_{CC} - 0.1 \ V \\ I_{out} \ \leq \ 20 \ \mu A \end{array}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	$\begin{array}{l} V_{out} = 0.1 \ V \\ I_{out} \ \leq \ 20 \ \mu A \end{array} \end{array}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V _{OH}	Minimum High-Level Output Voltage	$\begin{array}{l} V_{in} = V_{IH} \\ I_{out} \leq 20 \; \mu A \end{array}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
V _{OH}	Minimum High-Level Output Voltage	$\begin{array}{ll} V_{in} = V_{IH} & \left \begin{matrix} I_{out} \end{matrix} \right \leq 2.4 \ \text{mA} \\ \left \begin{matrix} I_{out} \end{matrix} \right \leq 6.0 \ \text{mA} \\ \left \begin{matrix} I_{out} \end{matrix} \right \leq 7.8 \ \text{mA} \end{array}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	V
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \le 20 \ \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{array}{ll} V_{in} = V_{IL} & \begin{array}{l} I_{out} \leq 2.4 \text{ mA} \\ I_{out} \leq 6.0 \text{ mA} \\ I_{out} \leq 7.8 \text{ mA} \end{array}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I _{OZ}	Maximum Three-State Leakage Current	Output in High–Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	6.0	±0.5	±5.0	±10	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $I_{out} = 0 \ \mu A$	6.0	4.0	40	40	μA

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

7. Information on typical parametric values can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		V _{CC}	Guara			
Symbol	Parameter	(V)	- 55 to 25°C	≤ 85°C	≤125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 3 and 6)	2.0 3.0 4.5 6.0	6.0 15 30 35	4.8 10 24 28	4.0 8.0 20 24	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q (Figures 3 and 6)	2.0 3.0 4.5 6.0	160 105 32 27	200 145 40 34	240 190 48 41	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Q (Figures 4 and 7)	2.0 3.0 4.5 6.0	150 100 30 26	190 125 38 33	225 150 45 38	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Q (Figures 4 and 7)	2.0 3.0 4.5 6 0	140 90 28 24	175 120 35 30	210 140 42 36	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, any Output (Figures 3 and 6)	2.0 3.0 4.5 6.0	60 27 12 10	75 32 15 13	90 36 18 15	ns
C _{in}	Maximum Input Capacitance	•	10	10	10	pF
Cout	Maximum Three-State Output Capacitance, Output in High- State	-Impedance	15	15	15	pF

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$; Input $t_r = t_f = 6.0 \text{ ns}$)

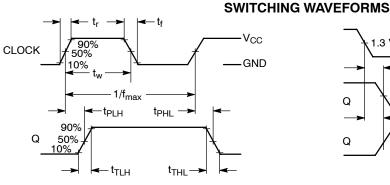
 For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Enabled Output)*	24	pF

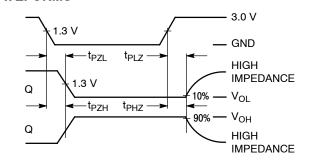
*Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (C_L = 50 pF; Input $t_r = t_f = 6.0$ ns)

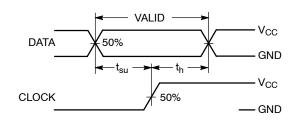
				Guaranteed Limit						
			v _{cc}	– 55 to	o 25°C	≤ 8	5°C	≤ 1 2	25°C	
Symbol	Parameter	Figure	(V)	Min	Max	Min	Max	Min	Max	Unit
t _{su}	Minimum Setup Time, Data to Clock	5	2.0 3.0 4.6 6.0	50 40 10 9.0		65 50 13 11		75 60 15 13		ns
t _h	Minimum Hold Time, Clock to Data	5	2.0 3.0 4.5 6.0	5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		ns
t _w	Minimum Pulse Width, Clock	3	2.0 3.0 4.5 6.0	75 60 15 13		95 80 19 16		110 90 22 19		ns
t _r , t _f	Maximum Input Rise and Fall Times	3	2.0 3.0 4.5 6.0		1000 800 500 400		1000 800 500 400		1000 800 500 400	ns



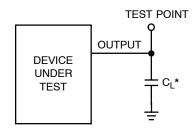






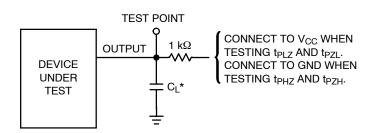






*Includes all probe and jig capacitance.

Figure 6.



*Includes all probe and jig capacitance.

Figure 7. Test Circuit

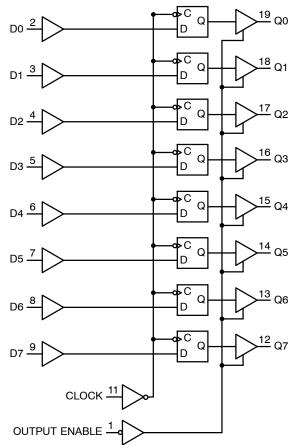
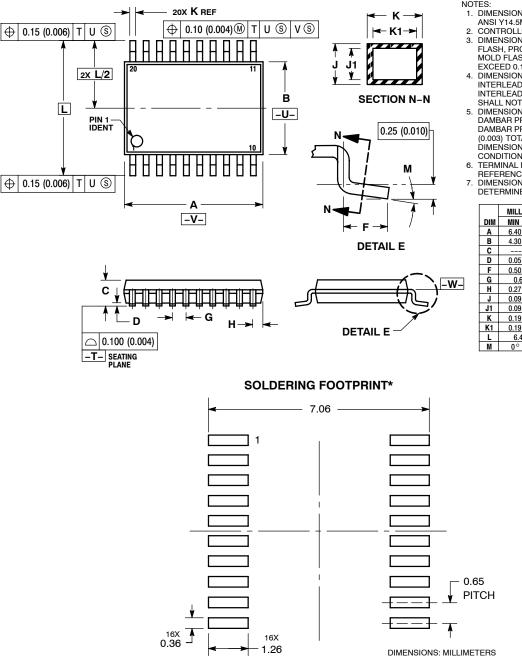


Figure 8. Expanded Logic Diagram

PACKAGE DIMENSIONS

TSSOP-20 CASE 948E-02 ISSUE C



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.

- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
Μ	0°	8°	0°	8°	

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